

32 Mbit Mobile FCRAM™

3.0 V, Page Mode

MB82DP02183F-65L

■ FEATURES

- Pseudo SRAM with Asynchronous SRAM Interface
- 8 Words Page Read Access Capability
- Byte Control by \overline{LB} , \overline{UB}
- Low Power Consumption
- Various Power Down Mode
 - Sleep
 - 4 Mbit Partial
 - 8 Mbit Partial
- Shipping Form: Chip / Wafer, 71-Pin FBGA package

■ MAIN SPECIFICATIONS

Part Number	MB82DP02183F-65L	
Organization	2 M Word × 16 bit	
Supply Voltage	2.6 V to 3.1 V	
Page Address Access Time (Max.)	20 ns	
Address Access Time (Max.)	65 ns	
Active Current (Max.)	30 mA	
Standby Current (Max.)	120 μA	
Power Down Current (Max.)	Sleep	10 μA

Note: FCRAM is a trademark of Fujitsu Microelectronics Limited, Japan.